NCE N-Channel Super Trench Power MOSFET

Description

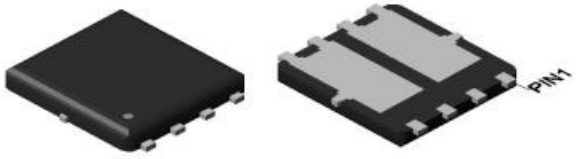
The NCEAP01ND35AG uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g. This device is ideal for high-frequency switching and synchronous rectification.

Application

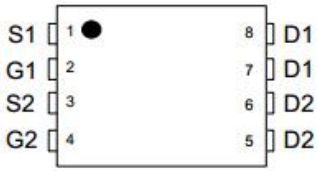
- Automotive application
- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

General Features

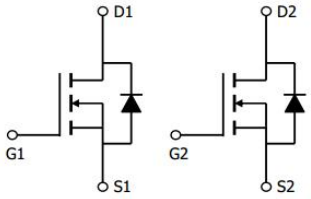
- V_{DS} =100V,I_D =35A
  $R_{DS(ON)}$=24mΩ (typical) @ V_{GS}=10V
  $R_{DS(ON)}$=27mΩ (typical) @ V_{GS}=4.5V
- Excellent gate charge x $R_{DS(on)}$ product(FOM)
- Very low on-resistance $R_{DS(on)}$
- 175 °C operating temperature
- Pb-free lead plating
- 100% UIS tested
- 100% ΔVds tested
- **AEC-Q101 qualified**



DFN 5X6-8L



Pin Assignment



Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
AP01ND35AG	NCEAP01ND35AG	DFN5X6-8L	-	-	-

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current-Continuous	I_D	35	A
	I_D (100℃)	24.5	A
Pulsed Drain Current	I_{DM}	140	A
Maximum Power Dissipation	P_D	60	W
Derating factor		0.4	W/℃
Single pulse avalanche energy (Note 1)	E_{AS}	200	mJ
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55 To 175	℃

Thermal Characteristic

Thermal Resistance,Junction-to-Case	$R_{\theta JC}$	2.5	℃/W

Electrical Characteristics (T_C=25℃unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250μA	100	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=100V,V_{GS}=0V	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±20V,V_{DS}=0V	-	-	±100	nA
On Characteristics						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250μA	1.2	2.0	2.8	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=10V,I_D=20A	-	24	28	mΩ
		V_{GS}=4.5V,I_D=20A	-	27	32	mΩ
Forward Transconductance	g_{FS}	V_{DS}=5V,I_D=20A	-	35	-	S
Dynamic Characteristics						
Input Capacitance	C_{lss}	V_{DS}=50V,V_{GS}=0V, F=1.0MHz	-	1600	-	pF
Output Capacitance	C_{oss}		-	139	-	pF
Reverse Transfer Capacitance	C_{rss}		-	11	-	pF
Switching Characteristics (Note 2)						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=50V,I_D=20A V_{GS}=10V,R_G=1.6Ω	-	6	-	nS
Turn-on Rise Time	t_r		-	2	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	18	-	nS
Turn-Off Fall Time	t_f		-	2	-	nS
Total Gate Charge	Q_g	V_{DS}=50V,I_D=20A, V_{GS}=10V	-	26	-	nC
Gate-Source Charge	Q_{gs}		-	7.4		nC
Gate-Drain Charge	Q_{gd}		-	3.8		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage	V_{SD}	V_{GS}=0V,I_S=35A	-	-	1.2	V
Diode Forward Current	I_S		-	-	35	A
Reverse Recovery Time	t_{rr}	T_J = 25°C, I_F = 20A di/dt = 500A/μs	-	26	-	nS
Reverse Recovery Charge	Qrr		-	98	-	nC

Notes:

1. EAS condition : Tj=25℃,V_{DD}=30V,V_G=10V,L=0.5mH,Rg=25Ω
2. Guaranteed by design, not subject to production
3. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of TJ(MAX)=175°C. The SOA curve provides a single pulse rating.

Typical Electrical and Thermal Characteristics

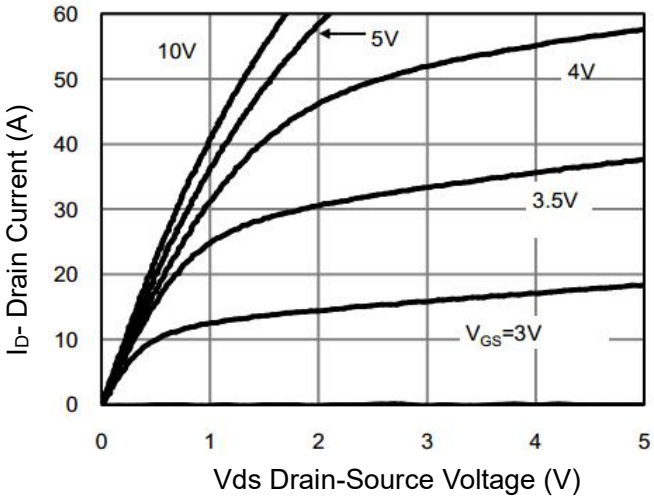


Figure 1 Output Characteristics

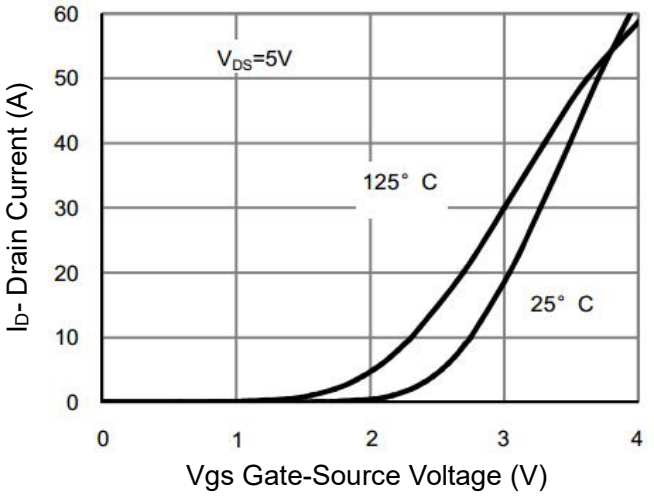


Figure 2 Transfer Characteristics

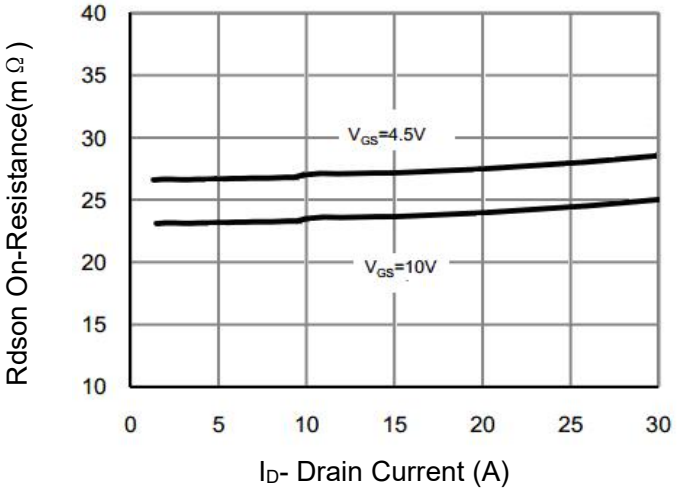


Figure 3 Rdson- Drain Current

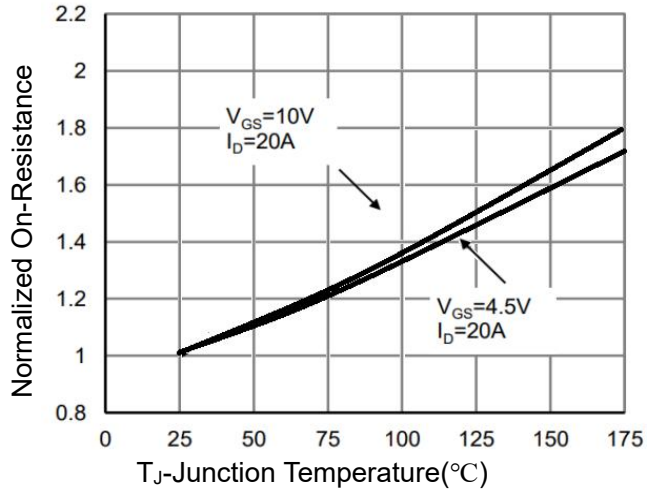


Figure 4 Rdson-Junction Temperature

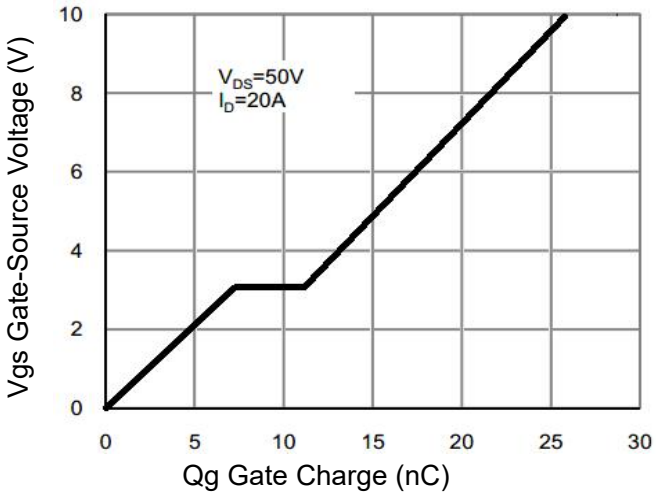


Figure 5 Gate Charge

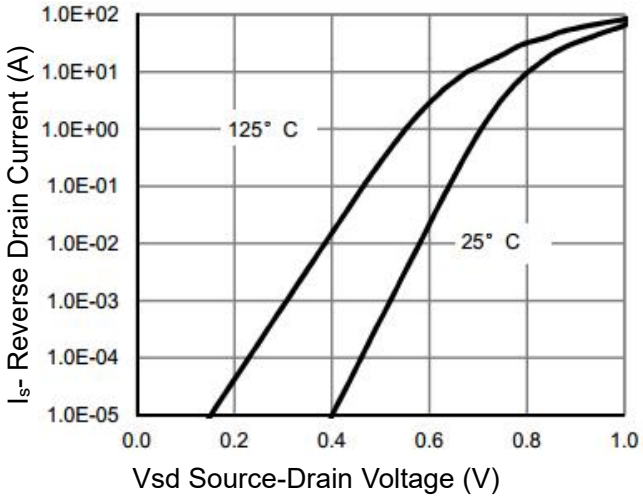


Figure 6 Source- Drain Diode Forward

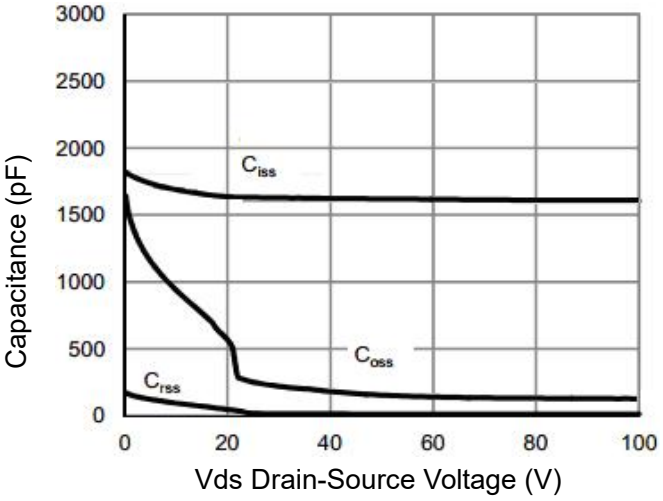


Figure 7 Capacitance vs Vds

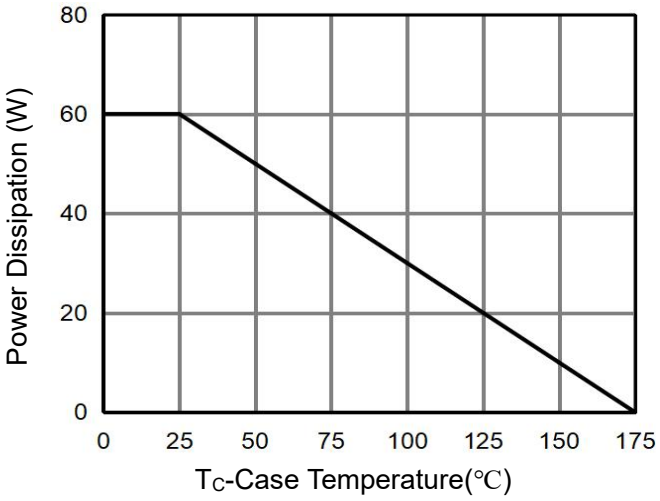


Figure 9 Power De-rating

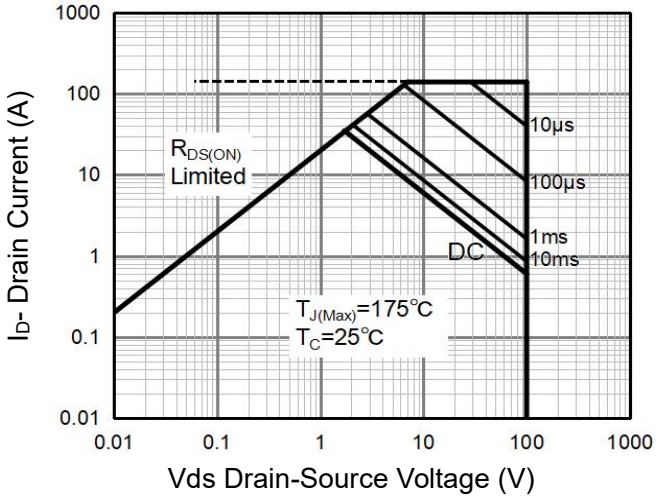


Figure 8 Safe Operation Area (Note3)

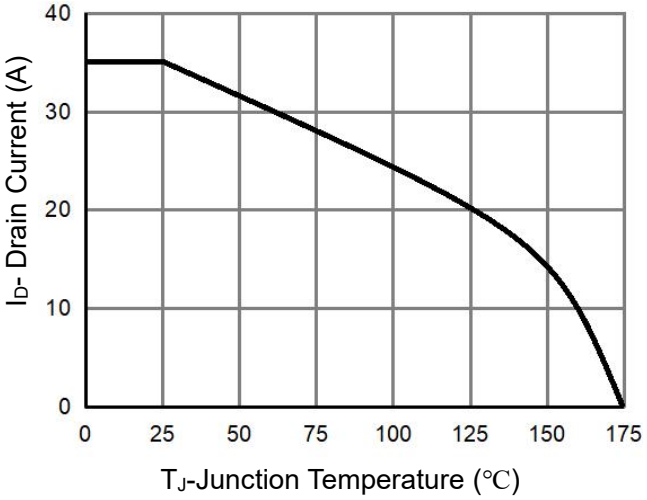


Figure 10 Current De-rating

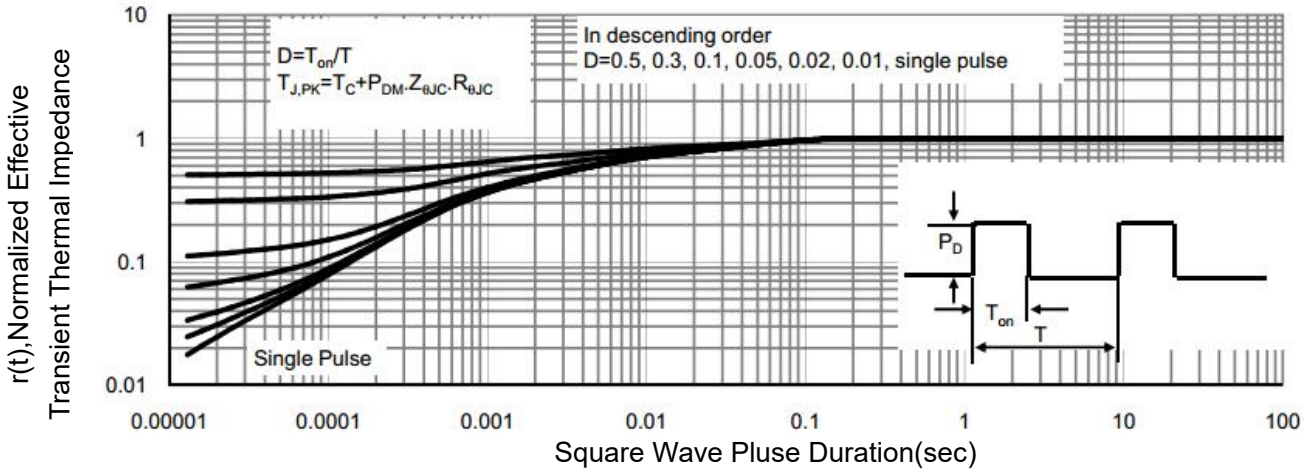
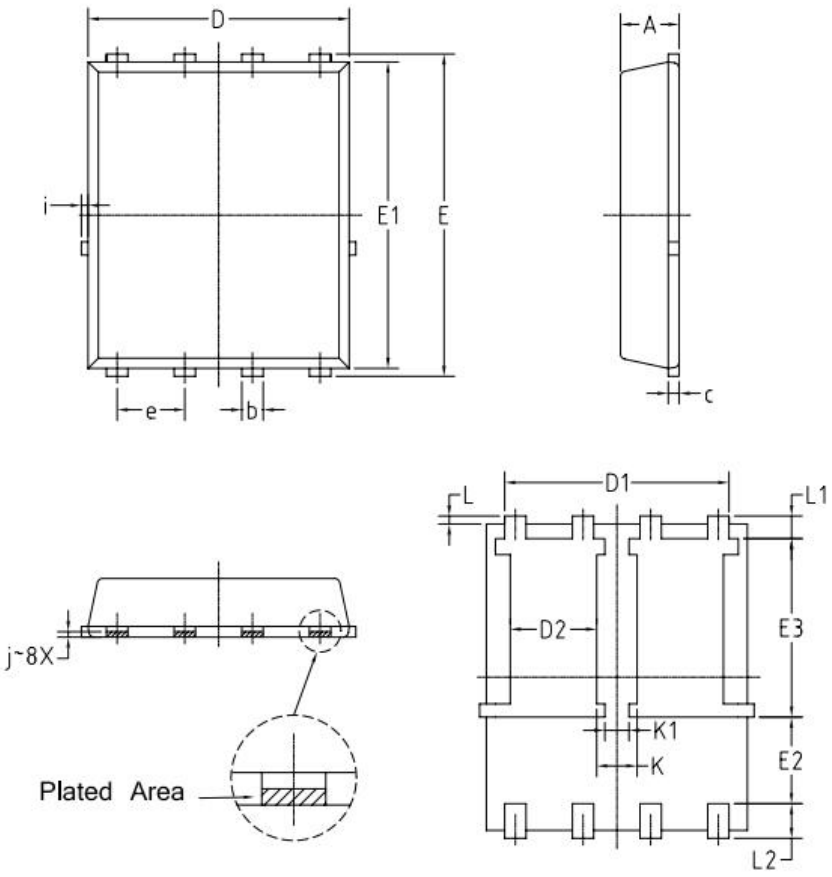


Figure 11 Normalized Maximum Transient Thermal Impedance

DFN5X6-8L Package Information



SYMBOL	COMMON			
	MM		INCH	
	MIN.	MAX.	MIN.	MAX.
A	1.00	1.20	0.039	0.047
b	0.30	0.50	0.012	0.020
c	0.203 BSC		0.008 BSC	
D	4.80	5.00	0.189	0.197
D1	4.06	4.36	0.160	0.172
D2	1.47	1.77	0.058	0.070
E	5.90	6.20	0.232	0.244
E1	5.65	5.85	0.222	0.230
E2	1.45	—	0.057	—
E3	3.20	3.50	0.126	0.138
e	1.27 BSC		0.05 BSC	
L	0.05	0.25	0.002	0.010
L1	0.325	0.525	0.013	0.021
L2	0.500	0.800	0.020	0.031
i	—	0.20	—	0.008
K	0.61	0.91	0.024	0.036
K1	0.31	0.60	0.012	0.024
j	0.1015 BSC		0.004BSC	

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